星合电子
XINGHE ELECTRONICS

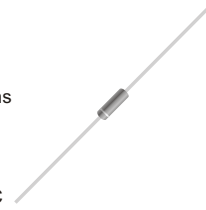
BAT19

SMALL SIGNAL SCHOTTKY DIODES

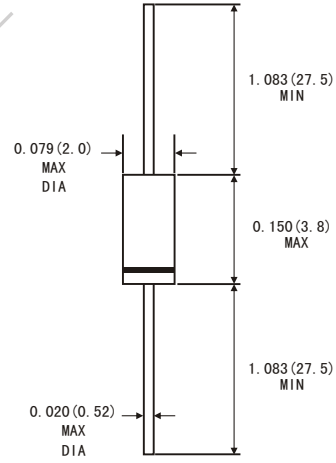
FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF mixers and ultrafast switching applications

  The diode is also available in the MiniMELF case with type designation LL19.
- High temperature soldering guaranteed:260℃/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



DO-35



Dimensions in inches and (millimeters)

MECHANICAL DATA

- *Case*: DO-35 glass case
- *Polarity:*color band denotes cathode end
- *Weight*: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V_{RRM}	10	V
Forward Continuous Current	I_F	30	mA
Surge non repetitive forward current $t_p \leqslant 1s$	I_{FSM}	60	mA
Junction and Storage temperature range	T_{STG} T_J	-65 to+150 -65 to+150	℃ ℃
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	T_L	230	℃

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakover voltage at I_R=10μA	V_R	10			V V
Leakage current at V_R=5V	I_R			100	nA
Forward voltage drop at I_F=1mA Test pulse: $t_p \leqslant 300\mu s$ $\delta < 2\%$ I_F=35mA	V_F V_F			0.40 1.0	V V
Junction Capacitance at V_R=0V ,f=1GHz	C_J			1.2	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

Figure 1. Forward current versus forward voltage at low level(typical values)

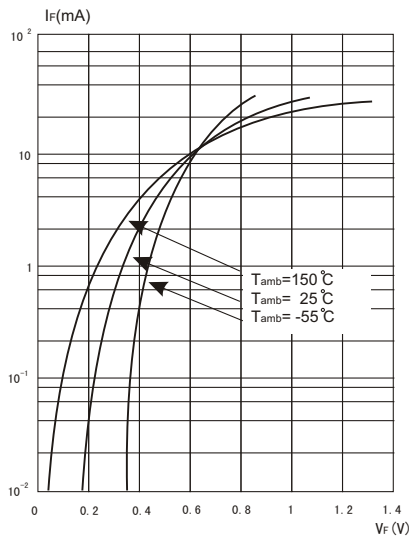


Figure 2. Capacitance C versus reverse applied voltage V_R (typical values)

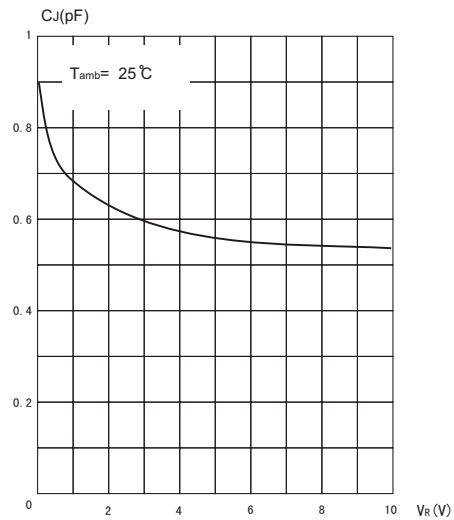


Figure 3.Reverse current versus ambient temperatures

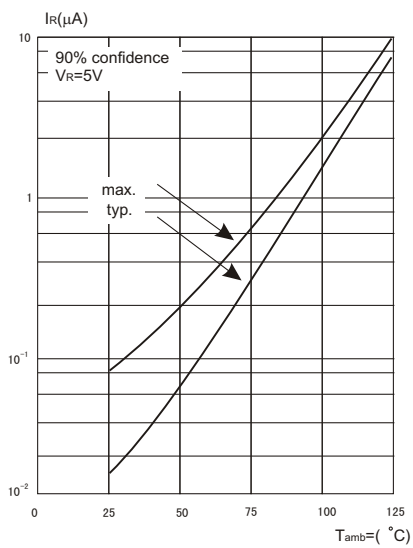


Figure 4.Reverse current versus continuous Reverse voltage(typical values)